

Title	Home institution	Host Institution
Grazing Incidence X-ray Diffraction (GIXRD) technique to study the structural properties of residual effects in GaN nanowires	Institute of Physics Polish Academy of Sciences, Poland	National Institute for Laser, Plasma and Radiation Physics, Romania
FeGa/MoSe ₂ /hBN and FeGa/Al ₂ O ₃ /MoSe ₂ /hBN magnetostriction effects on 2D materials	Bandırma Onyedi Eylül University, Turkey	University of Warsaw, Poland
Designing Multilayer Perovskite Oxides through Advanced Epitaxy for Enhanced Oxygen Evolution Electrocatalysts	AGH University of Science and Technology, Poland	University of Twente, The Netherlands
Advance XRD measurements for crystallographic phase identification in CdO/ZnO superlattices made by MBE	Institute of Physics Polish Academy of Sciences, Poland	National Institute for Laser, Plasma and Radiation Physics, Romania
Micro-Photoluminescence measurement of InAs _x P _{1-x} Quantum Dots in InP nanowires and their waveguiding effect	Scuola Normale superiore di Pisa, Italy	Wrocław University of Science and Technology, Poland
Investigating Anisotropic Thermal Conductivity in CVD Nanocrystalline Diamond for Enhanced Epitaxial Applications	Bandırma Onyedi Eylül University, Turkey	Universiteit Hasselt, Belgium
Fabrication and optical characterization of electrically triggered fully monolithic GaN-based single photon source device	ISOM, Universidad Politécnica de Madrid, Spain	Unipress, Warsaw, Poland
Epitaxial spin valve structures of functional La–Ba–Mn–Ti–O manganite for memory applications	ISSAT-MAHDIA, University of Monastir, Tunisia	National Institute of Materials Physics, Romania
Efficient active region for III-nitride based UV emitters	Institute of High Pressure Physics Polish Academy of Sciences, Poland	Quantum Photonics, Electronics and Engineering Laboratory (PHELIQS), CEA-IRIG, France
Spin Injection from Epitaxial Oxide Membrane into Semiconductor	Technion – Israel Institute of Technology, Israel	Technical University of Denmark, Denmark
Electroluminescence from Eu-doped ZnMgO Epilayers Grown by PA-MBE for Light Emitting Device Application	Institute of Physics Polish Academy of Sciences, Warsaw, Poland	Instituto Superior Técnico, Lisbon, Portugal
Engineering epitaxial ferroelectric/ relaxor ferroelectric heterostructure thin films for energy storage applications	University of Minho, Braga, Portugal	Institut de Ciència de Materials de Barcelona, Spain
Strain study of graphene as a suitable substrate for Zn ₃ P ₂ solar cells: A 4D-STEM approach	Catalan Institute of Nanoscience and Nanotechnology (ICN2), Spain	École Polytechnique Fédérale de Lausanne (EPFL), Switzerland
Growth of dilute bismides on GaSb nano-ridges by MOVPE	Strain study of graphene as a suitable substrate for Zn ₃ P ₂ solar cells: A 4D-STEM approach, Belgium	Philipps-Universität Marburg, Germany
Simulation of new epitaxial piezoelectric polymers	University of Aveiro, Portugal	University of Liverpool, United Kingdom
Epitaxy and Sputtering for the Development of BaZrO ₃ Thin Films	University of Ain-temouchent Belhadj Bouchaib, Algeria	University of Porto, Institute of Physics for Advanced Materials, Nanotechnology and Photonics, Portugal

Pattern formation in (a full-scale) epitaxy from the perspective of Cellular Automata	Université Clermont Auvergne, France	Sofia University, Bulgaria
Advances on Mist-CVD epitaxy for oxide compounds	IMEM-CNR, Italy	Department of Applied Physics and Electromagnetism of The Universitat De València, Spain
Bridging MOVPE and MBE Approaches for Advancing Rutile GeO ₂ Thin Film Epitaxy on TiO ₂ Substrates	Paul-Drude-Institut für Festkörperelektronik (PDI), Leibniz-Institut im Forschungsverbund Berlin e.V. Germany	University of Parma, Italy
Harnessing oxide membranes for flexible electronics	Paul Scherrer Institute (PSI), Switzerland	Technical University of Denmark (DTU), Denmark
Formation of Al and AlN on 7x7 Si(111) surface: Early-Stage Growth Dynamics by Molecular Beam Epitaxy	Institute of Physics of Materials of the Czech Academy of Sciences, Czech Republic	Paul Drude Institute for Solid State Electronics, Germany
Fabrication and optical characterization of GaN-InGaN-GaN single photon sources grown by Plasma-Assisted Molecular Beam Epitaxy	ISOM, Polytechnic University of Madrid, Spain	Unipress, Warsaw, Poland
Impact of RF-N ₂ plasma source design on the quality of dilute-nitride compounds grown by molecular beam epitaxy	Institute for Optoelectronic Systems and Microtechnology (ISOM), Universidad Politécnica de Madrid, Spain	Institut FOTON-CNRS-INSA, University of Rennes, France
Molecular Beam Epitaxial Growth (MBE) and Characterization of Rutile r-GeO ₂ Layers on Different r-TiO ₂ Substrate Orientation	University of Parma (UniPR), Italy	Paul-Drude-Institut für Festkörperelektronik (PDI), Germany
Integration of altermagnetic chromium antimonide on epitaxial ferroelectric germanium telluride on silicon	Department of Materials Science, University of Milano-Bicocca, Italy	Institute of Physics of the Czech Academy of Sciences, Czech Republic
In-Situ Tracking of Oxygen Vacancy Migration in MIEC Platforms for Synaptic Transistors Using 2D-OTR *	Catalonia Institute for Energy Research (IREC), Spain	University of Illinois Urbana-Champaign, United States of America
Exploring Emerging TEM/STEM Techniques for III-V Nanostructures in Quantum Communication and Space Photovoltaics	Universidad Carlos III de Madrid, Spain	CNRS-CHREA/ Université Côte d'Azur, France
Change of symmetry on perovskite thin films for nonlinear photonic modulators	Institut de Recerca en Energia de Catalunya (IREC), Spain	École Polytechnique Fédérale de Lausanne, Switzerland

(*) After being granted, this STSM was cancelled by grantee due to logistic reasons.